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	Affiliation	Soongsil University Department of Materials Science and Engineering	Position	Assistant Professor
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<b>Research Area</b>	<ul><li>Thin film process</li><li>Multicomponent ALD</li><li>Memory device</li></ul>			
Education	(2009) Seoul National University, Department of Materials Science and Engineering, B.S.			
	(2014) Seoul National University, Department of Materials Science and Engineering, Ph.D.			
Work Experience	(2014-2015) Seoul National University, Inter-university Semiconductor Research Center, Research Assistant			
	(2015-2018) Northwestern University, Materials Research Institute, Postdoctoral Fellow			
	(2018-2019) Northwestern University, Materials Research Institute, Research Associate			
	(2019-2022) Myongji University, Department of Electrical Engineering, Assistant Professor			
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## [Short bio]

**Woongkyu Lee** is an assistant professor in the Department of Materials Science and Engineering at Soongsil University. He earned his Ph.D. from the Department of Materials Science and Engineering of Seoul National University in 2014. He was a research assistant at Inter-University Semiconductor Research Center (Seoul National University, 2014-2015) and a postdoctoral fellow/research associate at Materials Research Institute (Northwestern University, 2015-2019). Before he joined Soongsil University in 2022, he worked at the Department of Electrical Engineering at Myongji University as an assistant professor. His research interests are focused on the thin film process, mainly the atomic layer deposition technique. Challenging materials with thermodynamically unstable phases or multicomponent materials were studied with novel precursors and reactants. Reaction mechanisms including interface/surface reaction and abnormal growth behavior were studied for DRAM capacitor, memristor, and flash applications.